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TITLE: EQUIPMENT FOR GROWING THIN FILM
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INVENTOR-INFORMATION:

NAME	COUNTRY
HONMA, TADAAKI	N/A
ARAI, TAKESHI	N/A

ASSIGNEE-INFORMATION:

NAME	COUNTRY
SHIN ETSU HANDOTAI CO LTD	N/A

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ABSTRACT:

PROBLEM TO BE SOLVED: To improve the uniformity of temp. within the surface of a susceptor throughout the surface and to uniformize the film thickness of the silicon single crystal thin film, in an equipment for vapor growth of a silicon single crystal thin film.

SOLUTION: In this equipment, the base material of lift pins 8 each embedded in a spot-faced part 5a of a susceptor 5 is changed from a conventional material to a material having a lower thermal conductivity value than that of

the base material of the susceptor 5 to prevent local temp.
drop in the
susceptor 5 from being caused in the vicinity of each of
the lift pins 8. As
the changed base material of the lift pins 8, SiC,
graphite, glassy carbon or
quartz is appropriately used and in particular, such a
material having a

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